

Silicon PNP Power Transistors

2SA483

DESCRIPTION

- With TO-66 package
- Complement to type 2SC783
- High voltage: $V_{CEO}=-150V(\text{min})$

APPLICATIONS

- Power amplifier applications
- Vertical output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

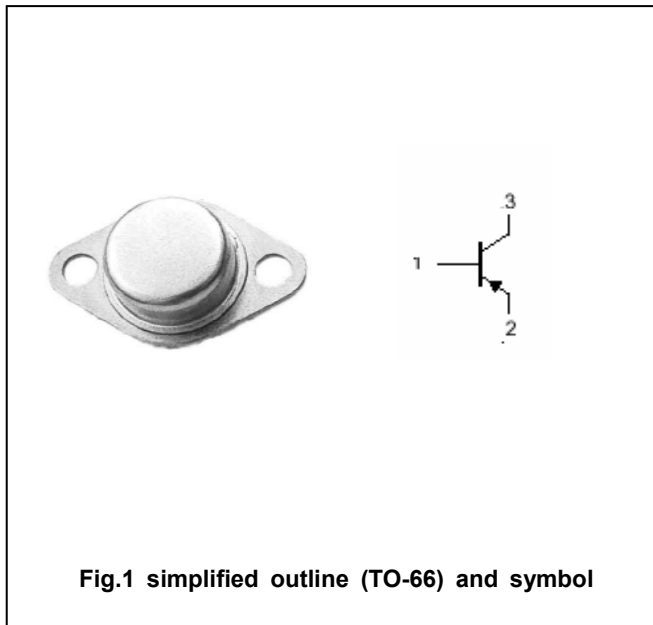


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_E	Emitter current		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ$	20	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

Silicon PNP Power Transistors

2SA483

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-0.5mA ; I _E =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A ; I _B =-50mA			-1.8	V
V _{BE}	Base-emitter on voltage	I _C =-0.5A ; V _{CE} =-10V			-1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-0.1A ; V _{CE} =-10V	30		240	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-10V ; f=1.0MHz		50		pF
f _T	Transition frequency	I _C =-0.1A ; V _{CE} =-10V		10		MHz

◆ h_{FE} Classifications

R	O	Y
30-80	70-140	120-240

Silicon PNP Power Transistors

2SA483

PACKAGE OUTLINE



Fig.2 outline dimensions